Unit: mm

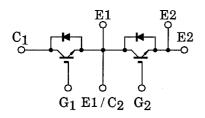
TOSHIBA GTR Module Silicon N Channel IGBT

# MG30V2YS40

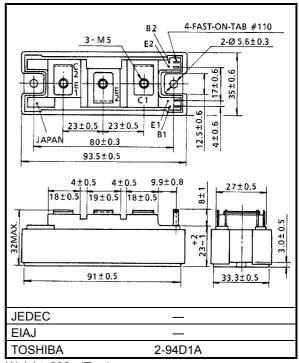
High Power Switching Applications Motor Control Applications

- The electrodes are isolated from case.
- High input impedance
- Includes a complete half bridge in one package.
- Enhancement-mode
- High speed :  $t_f = 1.5 \mu s$  (Max.) (IC = 30A)  $t_{rr} = 0.3 \mu s$  (Max.) (IF = 30A)

#### **Equivalent Circuit**



#### Maximum Ratings (Ta = 25°C)



Weight: 202g (Typ.)

Characteris	Symbol	Rating	Unit		
Collector-emitter voltage		V <sub>CES</sub>	1700	V	
Gate-emitter voltage		V <sub>GES</sub>	±20	V	
Collector current	DC	Ι <sub>C</sub>	30	^	
	1ms	I <sub>CP</sub>	60	A	
Forward current	DC	١ <sub>F</sub>	30	A	
	1ms	I <sub>FM</sub>	60		
Collector power dissipation (Tc = 25°C)		PC	500	W	
Junction temperature		Тj	150	°C	
Storage temperature range		T <sub>stg</sub>	-40 ~ 125	°C	
Isolation voltage		V <sub>Isol</sub>	4000 (AC 1 min.)	V	
Screw torque (Terminal / mounting)		—	3/3	N∙m	

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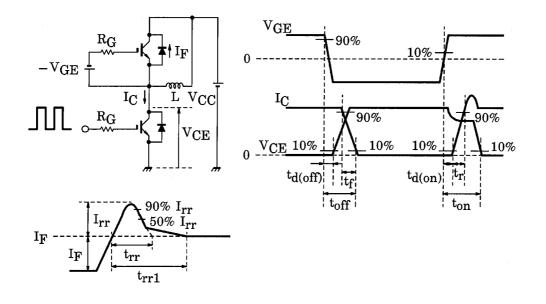
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**Electrical Characteristics (Ta = 25°C)** 

Cł	naracteristic	Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current		I <sub>GES</sub>	$V_{GE}$ = ±20V, $V_{CE}$ = 0		_	_	±50	nA
Collector cut-off current		ICES	V <sub>CE</sub> = 1700V, V <sub>GE</sub> = 0			_	0.5	mA
Gate-emitter cut-off voltage		V <sub>GE (off)</sub>	I <sub>C</sub> = 30mA, V <sub>CE</sub> = 5V		4.0	_	8.0	V
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	I <sub>C</sub> = 30A, V <sub>GE</sub> = 15V		_	3.2	4.5	V
Input capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0, f = 1MHz		_	4400	_	pF
Switching time	Turn-on delay time	t <sub>d (on)</sub>			_	0.1		-
	Rise time	t <sub>r</sub>	Inductive load $V_{CC} = 900V$ $I_C = 30A$ $V_{GE} = \pm 15V$ $R_G = 24\Omega$		_	0.1		
	Turn-on time	t <sub>on</sub>			_	0.5		
	Turn-off delay time	t <sub>d (off)</sub>		(Note 1)	_	0.4		- µs
	Fall time	t <sub>f</sub>			_	0.5	1.5	
	Turn-off time	t <sub>off</sub>				1.0		
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 30 A, V <sub>GE</sub> = 0			3.2	4.5	V
Reverse recovery time		t <sub>rr</sub>	$I_F = 30 \text{ A}, V_{GE} = -15 \text{ V},$ di / dt = 500 A / $\mu$ s (	(Note 1)	_	0.1	0.3	μs
Thermal resistance		R <sub>th (j-c)</sub>	Transistor stage		_	—	0.25	°C/W
			Diode stage		_	—	1.0	

Note 1: Switching time and reverse recovery time test circuit & timing chart

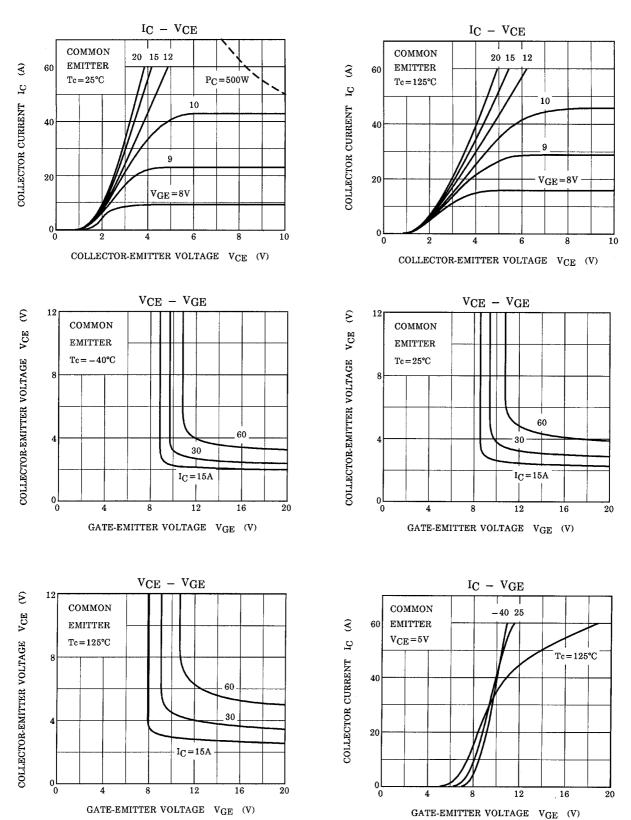


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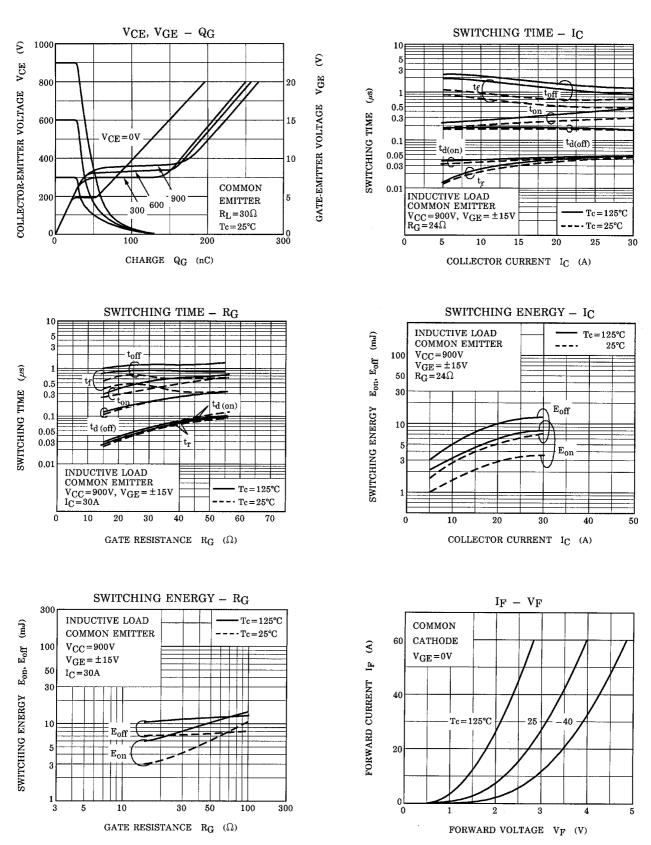
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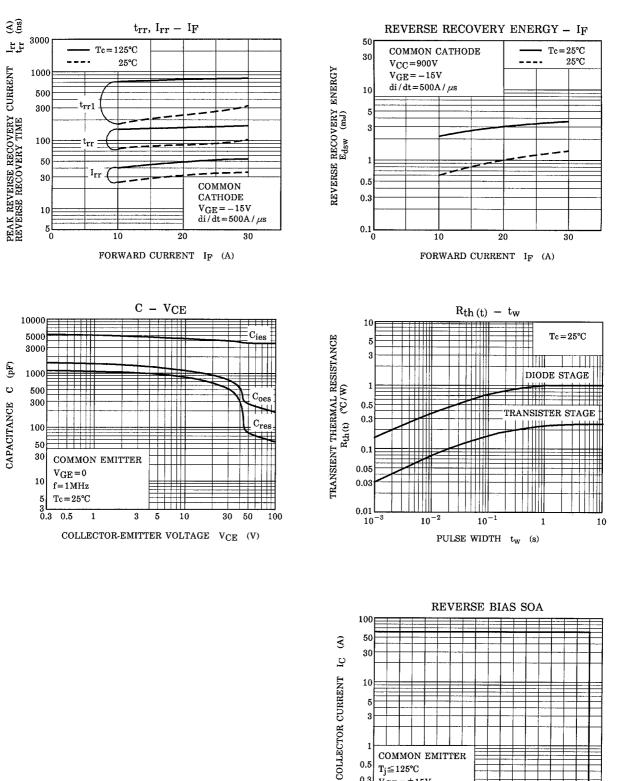
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0.3

0.1L 0

 $V_{GE} = \pm 15V$  $R_G = 24\Omega$ 

> 200 400 600 800 1000 1200 1400 1600 1800 Collector-emitter voltage  $v_{CE}$  (V)